LDMOS 3-stage integrated Doherty MMIC

AMPLEON

Rev. 1 — 18 September 2020

Product data sheet

1. Product profile

1.1 General description

The BLM10D3438-70ABG is a 3-stage fully integrated Doherty MMIC solution using Ampleon's state of the art GEN10 LDMOS technology. The carrier and peaking device, input splitter and output combiner are integrated in a single package. This multiband device is perfectly suited as general purpose driver or mMIMO final in the frequency range from 3400 MHz to 3800 MHz. Available in gull wing.

Table 1. Performance

Typical RF performance at T_{case} = 25 °C; I_{Dq} = 110 mA (carrier); V_{GSq(peaking)} = V_{GSq(peaking)} - 0.5 V.

| Test signal | f | V _{DS} | P _{L(M)} | Gp | ησ | ACPR _{20M} |
|----------------------|-------|-----------------|-------------------|------|------|---------------------|
| | (MHz) | (V) | (dBm) | (dB) | (%) | (dBc) |
| 1-carrier LTE 20 MHz | 3600 | 28 | 40 | 31.8 | 37.8 | -24 |

1.2 Features and benefits

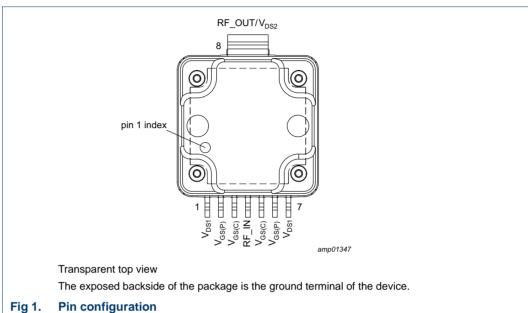
- Integrated input splitter
- Integrated output combiner
- High efficiency
- Designed for broadband operation (frequency 3400 MHz to 3800 MHz)
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Source impedance 50 Ω; high power gain
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

■ RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 3400 MHz to 3800 MHz frequency range

2. Pinning information

2.1 Pinning



3 3 3 3 3

2.2 Pin description

Table 2. Pin description

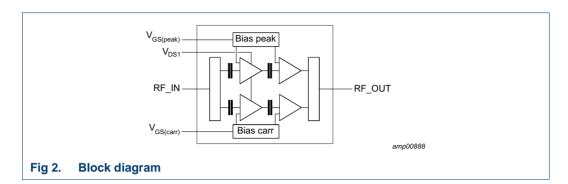
| Symbol | Pin | Description |
|-------------------------|--------|--|
| V _{DS1} | 1 | drain-source voltage of driver stages |
| $V_{GS(P)}$ | 2 | gate-source voltage of peaking P |
| V _{GS(C)} | 3 | gate-source voltage of carrier C |
| RF_IN | 4 | RF input |
| V _{GS(C)} | 5 | gate-source voltage of carrier C |
| $V_{GS(P)}$ | 6 | gate-source voltage of peaking P |
| V _{DS1} | 7 | drain-source voltage of driver stages |
| RF_OUT/V _{DS2} | 8 | RF output / drain-source voltage of final stages |
| GND | flange | RF ground |

3. Ordering information

Table 3. Ordering information

| Type number | Packag | ackage | | |
|------------------|--------|--|--------------|--|
| | Name | Description | Version | |
| BLM10D3438-70ABG | | plastic, heatsink small outline package; 8 leads | OMP-400-8G-1 | |

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-------------------|----------------------|------------|-----|------|------|
| V _{DS} | drain-source voltage | | - | 65 | V |
| V_{GS} | gate-source voltage | | -6 | +9 | V |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | [1] | - | 200 | °C |
| T _{case} | case temperature | | - | 150 | °C |

Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Measured for total device.

| Symbol | Parameter | Conditions | Value | Unit |
|----------------------|-------------------------------------|---|-------|------|
| R _{th(j-c)} | thermal resistance from junction to | $T_{case} = 90 ^{\circ}C; P_{L} = 6.3 W$ [1] | 1.88 | K/W |
| | case | $T_{case} = 90 ^{\circ}C; P_{L} = 10 W$ [1] | 1.51 | K/W |

^[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

Characteristics 7.

Table 6. **DC** characteristics

 $T_{\rm case} = 25 \, ^{\circ}{\rm C}$.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------|-------------------------------|---|-----|-----|-----|------|
| Carrier | | | | | | |
| V_{GSq} | gate-source quiescent voltage | $V_{DS} = 28 \text{ V}; I_D = 110 \text{ mA}$ | 1.6 | 2.2 | 2.7 | V |
| I _{GSS} | gate leakage current | V _{GS} = 1 V; V _{DS} = 0 V | - | - | 140 | nA |
| Peaking | | | | | | |
| I _{GSS} | gate leakage current | V _{GS} = 1 V; V _{DS} = 0 V | - | - | 140 | nA |
| Final sta | ges | | | | | |
| I _{DSS} | drain leakage current | $V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$ | - | - | 1.4 | μΑ |
| Driver st | ages | | | | | |
| I _{DSS} | drain leakage current | V _{GS} = 0 V; V _{DS} = 28 V | - | - | 1.4 | μΑ |

RF Characteristics

Typical RF performance at $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 110$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5 \text{ V}; P_{L(AV)} = 10 \text{ W}; unless otherwise specified measured in an$ Ampleon production circuit.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit | |
|---------------------|---------------------------------------|--------------------------------|------|------|------|------|--|
| Test sign | Test signal: pulsed CW [1] | | | | | | |
| G _p | power gain | f = 3600 MHz | 29.5 | 31.5 | 33.5 | dB | |
| η_{D} | drain efficiency | P _L = 10 W (40 dBm) | 33 | 42 | - | % | |
| | | $P_L = P_{L(3dB)}$ | 34 | 41 | - | % | |
| RL _{in} | input return loss | | - | -15 | -10 | dB | |
| P _{L(3dB)} | output power at 3 dB gain compression | | 47.4 | 48.2 | - | dBm | |

^[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s)

Application information

Typical performance

T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 110 mA (driver and final stages); test signal: 1-carrier LTE 20 MHz, PAR 7.6 dB at 0.01 % probability CCDF; measured in an Ampleon 3400 MHz to 3800 MHz frequency band asymmetrical integrated Doherty application circuit.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--|---------------------------------------|--|-----|-------|-----|------|
| P _{L(3dB)} | output power at 3 dB gain compression | f = 3600 MHz | - | 48.6 | - | dBm |
| φ _{s21} /φ _{s21(norm)} | normalized phase response | at 3 dB compression point; f = 3600 MHz | - | -55.4 | - | 0 |
| η _D | drain efficiency | 8.6 dB OBO (P _{L(AV)} = 40 dBm); f = 3600 MHz | - | 37.3 | - | % |
| G _p | power gain | P _{L(AV)} = 40 dBm; f = 3600 MHz | - | 31.8 | - | dB |
| B _{video} | video bandwidth | P _{L(AV)} = 40 dBm, set to obtain IMD3 = -40 dBc; 2-tone CW; f = 3600 MHz | - | >600 | - | MHz |
| G _{flat} | gain flatness | P _{L(AV)} = 40 dBm; f = 3400 MHz to 3800 MHz | - | 0.5 | - | dB |

BLM10D3438-70ABG

LDMOS 3-stage integrated Doherty MMIC

Table 8. Typical performance ...continued

 $T_{\rm case}$ = 25 °C; $V_{\rm DS}$ = 28 V; $I_{\rm Dq}$ = 110 mA (driver and final stages); test signal: 1-carrier LTE 20 MHz, PAR 7.6 dB at 0.01 % probability CCDF; measured in an Ampleon 3400 MHz to 3800 MHz frequency band asymmetrical integrated Doherty application circuit.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|---------------------------------------|---|-----|-------|-----|-------|
| ACPR _{20M} | adjacent channel power ratio (20 MHz) | P _{L(AV)} = 40 dBm; f = 3600 MHz | - | -24.4 | - | dBc |
| ΔG/ΔT | gain variation with temperature | f = 3600 MHz [3] | - | 0.06 | - | dB/°C |
| К | Rollett stability factor | $T_{case} = -40$ °C; f = 0.2 GHz to 6 GHz | - | >1.5 | - | |

- [1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s).
- [2] 25 ms CW power sweep measurement.
- [3] S-parameters measured with broadband demo board.

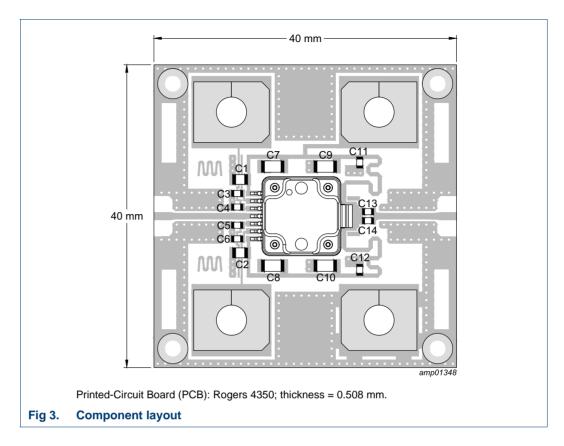
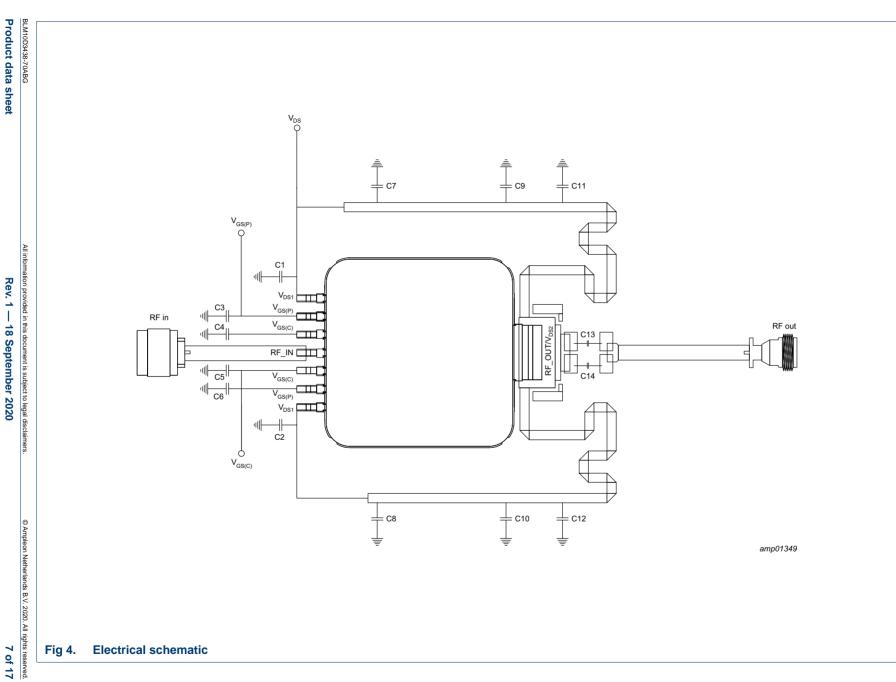


Table 9. Demo test circuit list of components

See <u>Figure 3</u> for component layout.

| Component | Description | Value | Remarks |
|-----------------|-----------------------------------|--------------|---------|
| C1, C2 | multilayer ceramic chip capacitor | 4.7 μF, 35 V | TDK |
| C3, C4, C5, C6 | multilayer ceramic chip capacitor | 1 μF, 6.3 V | Murata |
| C7, C8, C9, C10 | multilayer ceramic chip capacitor | 10 μF, 50 V | Murata |
| C11, C12 | multilayer ceramic chip capacitor | 3 pF | Murata |
| C13, C14 | multilayer ceramic chip capacitor | 4.7 pF | Murata |



Product data sheet

8.1 Ruggedness in a Doherty operation

The BLM10D3438-70ABG is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: $V_{DS} = 32 \text{ V}$; $I_{Dq} = 110 \text{ mA (carrier)}$; $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.5 \text{ V}$; P_i corresponding to $P_{L(3dB)} - 5 \text{ dB}$ under $Z_S = 50 \Omega$ load; f = 3800 MHz (1-carrier W-CDMA signal with PAR = 9.9 dB); $T_{case} = 25 \,^{\circ}\text{C}$ unless otherwise specified.

8.2 Impedance information

Table 10. Typical impedance for optimum Doherty operation

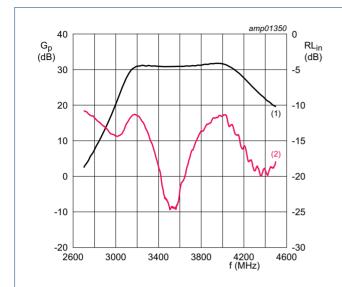
Measured load-pull data per section; test signal: pulsed CW; T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 110 mA (carrier); $V_{GSq(peaking)}$ = $V_{GSq(carrier)}$ – 0.5 V; t_p = 100 μ s; δ = 10 %. Typical values unless otherwise specified.

| | tuned for optimum Doherty operation | | | | |
|-------|-------------------------------------|---------------------|---------------------|----------------------|----------------------|
| f | Z _L | G _{p(max)} | P _{L(3dB)} | η _{add} [1] | η _{add} [2] |
| (MHz) | (Ω) | (dB) | (dBm) | (%) | (%) |
| 3400 | 19.51 – j22.94 | 32.4 | 48.48 | 43.3 | 44.0 |
| 3500 | 19.86 – j19.85 | 32.0 | 48.59 | 44.1 | 45.0 |
| 3600 | 17.03 – j17.98 | 32.1 | 48.65 | 44.9 | 45.4 |
| 3700 | 15.13 – j18.50 | 32.2 | 48.67 | 45.5 | 45.1 |
| 3800 | 14.85 – j20.56 | 32.8 | 48.68 | 46.4 | 44.2 |

^[1] At 3 dB gain compression point.

^[2] At $P_L = 40 \text{ dBm}$.

8.3 Graphs



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 110$ mA (carrier and peaking stages);

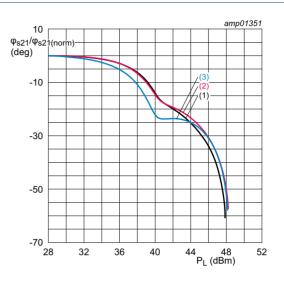
 $V_{GS} = 2.11 \text{ V (carrier stage)};$

V_{GS} = 1.61 V (peaking stage).

Test signal: CW.

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 5. Wideband power gain and input return loss as function of frequency; typical values



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

 $I_{Dq1} + I_{Dq2} = 110$ mA (carrier and peaking stages);

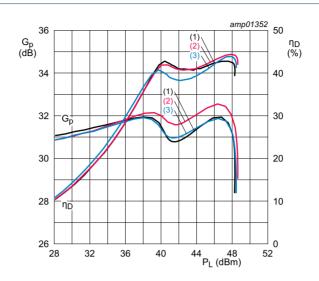
 $V_{GS} = 2.11 \text{ V (carrier stage)};$

V_{GS} = 1.61 V (peaking stage).

Test signal: 25 ms CW power sweep.

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

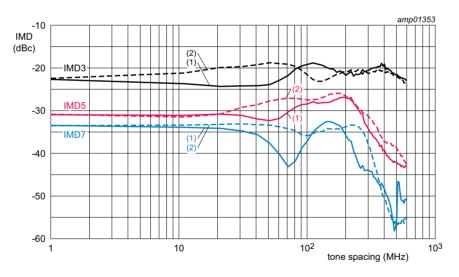
Fig 6. Normalized phase response as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 110 mA (carrier and peaking stages); V_{GS} = 2.11 V (carrier stage); V_{GS} = 1.61 V (peaking stage). Test signal: pulsed CW power sweep (δ = 10 %; t_p = 100 μs).

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

Fig 7. Power gain and drain efficiency as function of output power; typical values

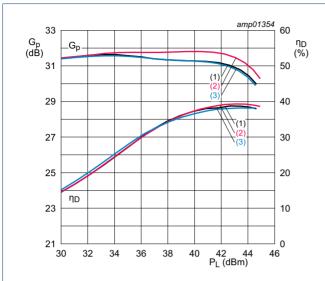


 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 110 mA (carrier and peaking stages); V_{GS} = 2.11 V (carrier stage); V_{GS} = 1.61 V (peaking stage). Test signal: 2-tone CW; f_{c} = 3600 MHz.

- (1) IMD low
- (2) IMD high

Fig 8. Intermodulation distortion as a function of tone spacing; typical values

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 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

 $I_{Dq1} + I_{Dq2} = 110$ mA (carrier and peaking stages);

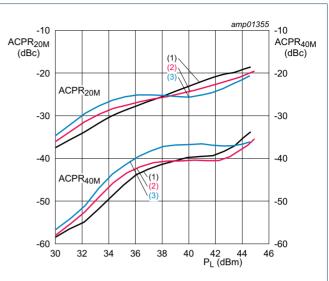
 $V_{GS} = 2.11 \text{ V (carrier stage)};$

 $V_{GS} = 1.61 \text{ V (peaking stage)}.$

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

Fig 9. Power gain and drain efficiency as function of output power; typical values



 $T_{case} = 25 \, ^{\circ}C; \, V_{DS} = 28 \, V;$

 $I_{Dq1} + I_{Dq2} = 110$ mA (carrier and peaking stages);

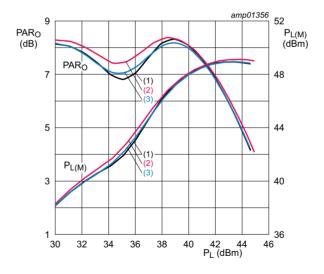
 $V_{GS} = 2.11 \text{ V (carrier stage)};$

V_{GS} = 1.61 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

Fig 10. Adjacent channel power ratio as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 110 mA (carrier and peaking stages);

 $V_{GS} = 2.11 \text{ V (carrier stage)}$; $V_{GS} = 1.61 \text{ V (peaking stage)}$.

Test signal: 1-carrier LTE; PAR = 7.6 dB at 0.01 % probability CCDF.

- (1) f = 3400 MHz
- (2) f = 3600 MHz
- (3) f = 3800 MHz

Fig 11. Output peak-to-average ratio and peak output power as function of output power; typical values

9. Package outline

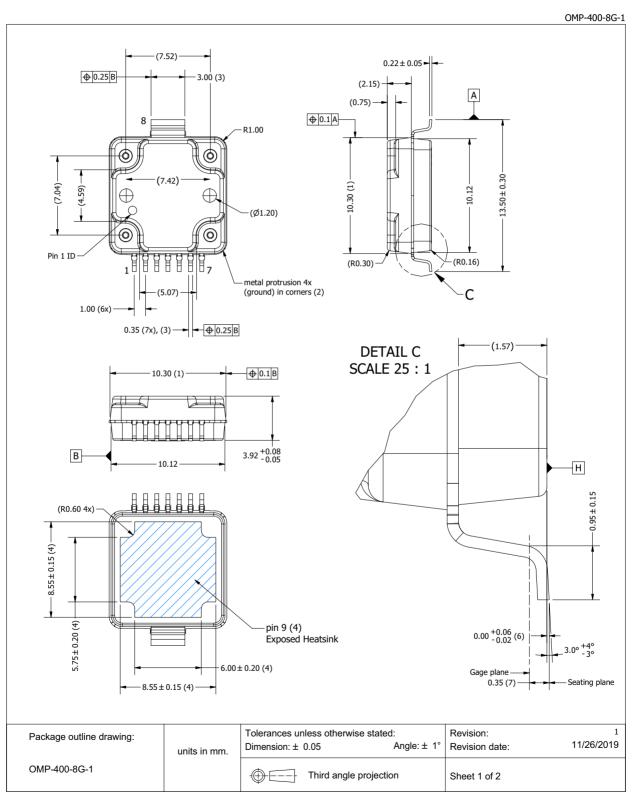


Fig 12. Package outline OMP-400-8G-1 (sheet 1 of 2)

OMP-400-8G-1

| | Drawing Notes |
|-------|--|
| Items | Description |
| | Dimensions are excluding mold protrusion. Areas located adjacent to the leads have a maximum mold protrusion of 0.25 |
| (1) | mm (per side) and 0.62 mm max. in length. In between the 7 leads the protrusion is 0.25 mm max. At all other areas the |
| | mold protrusion is maximum 0.15 mm per side. See also detail B. |
| (2) | The metal protrusion (tie bars) in the corner will not stick out of the molding compound protrusions (detail A). |
| (3) | The lead dambar (metal) protrusions are not included. Add 0.14 mm max to the total lead dimension at the dambar location |
| (4) | The hatched area indicates the exposed heatsink. The dimensions represent the values between two opposite points alor |
| (4) | the original heatsink perimeter. |
| (5) | The leads and exposed heatsink are plated with matte Tin (Sn). |
| (C) | Dimension is measured with respect to the bottom of the heatsink Datum H. Positive value means that the bottom of the |
| (6) | heatsink is higher than the bottom of the lead. |
| (7) | Gage plane (foot length) to be measured from the seating plane. |

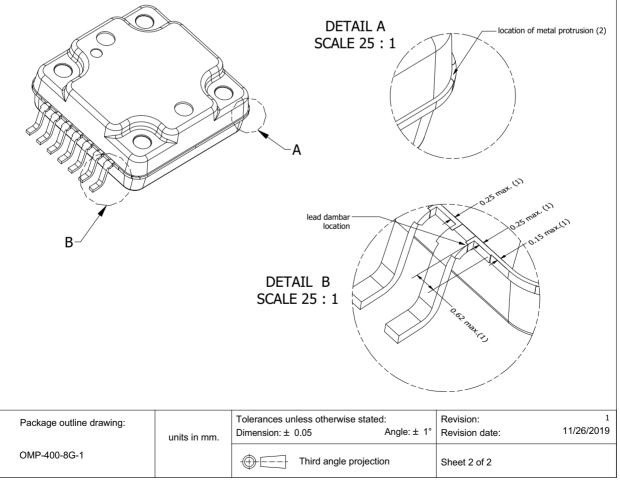


Fig 13. Package outline OMP-400-8G-1 (sheet 2 of 2)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

| ESD model | Class |
|--|--------|
| Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002 | C1 [1] |
| Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001 | 1B 🛂 |

- [1] CDM classification C1 is granted to any part that passes after exposure to an ESD pulse of 250 V.
- [2] HBM classification 1B is granted to any part that passes after exposure to an ESD pulse of 500 V.

11. Abbreviations

Table 12. Abbreviations

| Acronym | Description |
|---------|--|
| CW | Continuous Wave |
| ESD | ElectroStatic Discharge |
| GEN10 | Tenth Generation |
| GSM | Global System for Mobile Communications |
| LDMOS | Laterally Diffused Metal Oxide Semiconductor |
| LTE | Long Term Evolution |
| mMIMO | Massive Multiple Input-Multiple Output |
| MMIC | Monolithic Microwave Integrated Circuit |
| MTF | Median Time to Failure |
| ОВО | Output Back Off |
| PAR | Peak-to-Average Ratio |
| RoHS | Restriction of Hazardous Substances |
| VSWR | Voltage Standing Wave Ratio |
| W-CDMA | Wideband Code Division Multiple Access |

12. Revision history

Table 13. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------------|--------------|--------------------|---------------|------------|
| BLM10D3438-70ABG v.1 | 20200918 | Product data sheet | - | - |

13. Legal information

13.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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BLM10D3438-70ABG

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LDMOS 3-stage integrated Doherty MMIC

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